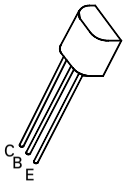
PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

ZTX789A

ISSUE 2 – APRIL 94

FEATURES
* 25 Volt V_{CEO}
* Gain of 200 at I_C=2 Amps
* Very low saturation voltage

APPLICATIONS
* Darlington replacement
* Battery powered circuits
* Motor drivers



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-25	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-8	A
Continuous Collector Current	I_C	-3	A
Practical Power Dissipation*	P_{totp}	1.5	W
Power Dissipation at T_{amb}=25°C derate above 25°C	P_{tot}	1 5.7	W mW/°C
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +200	°C

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-25			V	I_C=-100μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-25			V	I_C=-10mA*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	I_E=-100μA
Collector Cut-Off Current	I_{CBO}			-0.1	μA	V_{CB}=-15V
Emitter Cut-Off Current	I_{EBO}			-0.1	μA	V_{EB}=-4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.25 -0.45 -0.5	V V V	I_C=-1A, I_B=-10mA* I_C=-2A, I_B=-20mA* I_C=-3A, I_B=-100mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.0	V	I_C=-1A, I_B=-10mA*
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.8		V	IC=-1A, V_{CE}=-2V*
Static Forward Current Transfer Ratio	h_{FE}	300 250 200 100		800		I_C=-10mA, V_{CE}=-2V I_C=-1A, V_{CE}=-2V* I_C=-2A, V_{CE}=-2V* I_C=-6A, V_{CE}=-2V*

ZTX789A

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C)

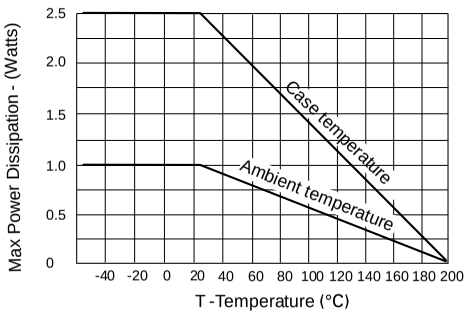
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Transition Frequency	f_T	100			MHz	I_C=-50mA, V_{CE}=-5V f=50MHz
Input Capacitance	C_{ibo}		225		pF	V_{EB}=-0.5V, f=1MHz
Output Capacitance	C_{obo}		25		pF	V_{CB}=-10V, f=1MHz
Switching Times	t_{on} t_{off}		35 400		ns ns	I_C=-500mA, I_{B1}=-50mA I_{B2}=-50mA, V_{CC}=-10V

*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤2%

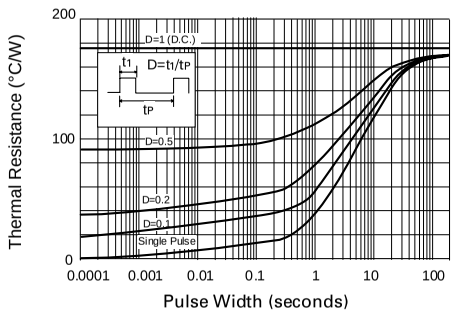
THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient$_1$	$R_{th(j-amb)1}$	175	°C/W
Junction to Ambient$_2$	$R_{th(j-amb)2}$†	116	°C/W
Junction to Case	$R_{th(j-case)}$	70	°C/W

† Device mounted on P.C.B. with copper equal to 1 sq. Inch minimum.



Derating curve



Maximum transient thermal impedance

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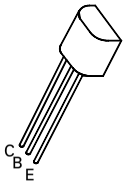

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Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.8		V	IC=-1A, V_{CE}=-2V*
Static Forward Current Transfer Ratio	h_{FE}	300 250 200 100		800		I_C=-10mA, V_{CE}=-2V I_C=-1A, V_{CE}=-2V* I_C=-2A, V_{CE}=-2V* I_C=-6A, V_{CE}=-2V*

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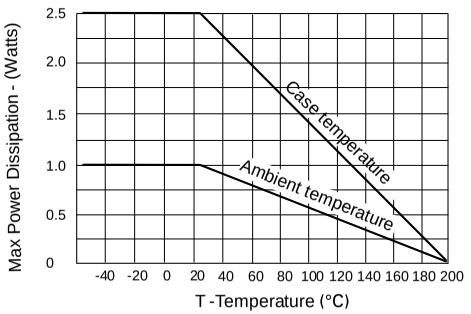

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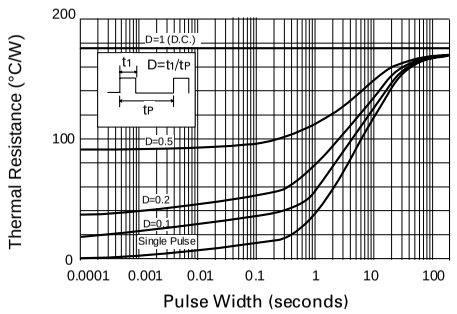
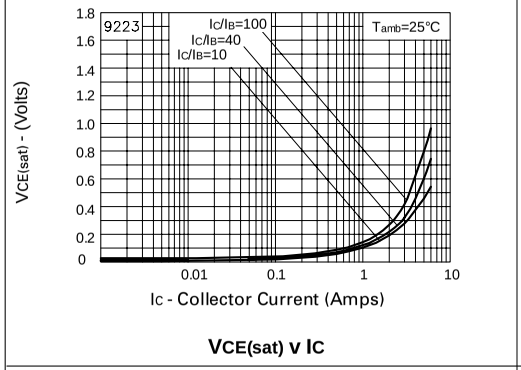


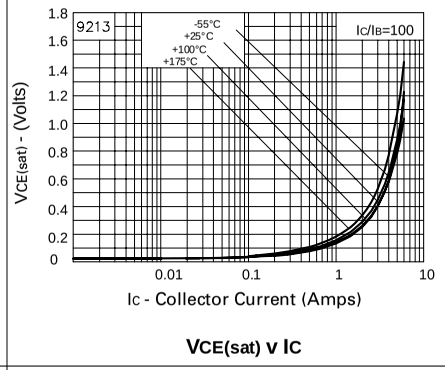
Maximum transient thermal impedance

ZTX789A

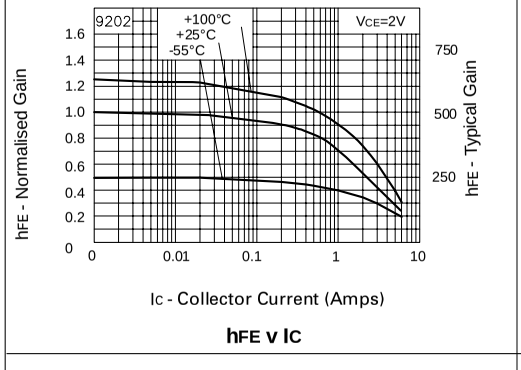
TYPICAL CHARACTERISTICS



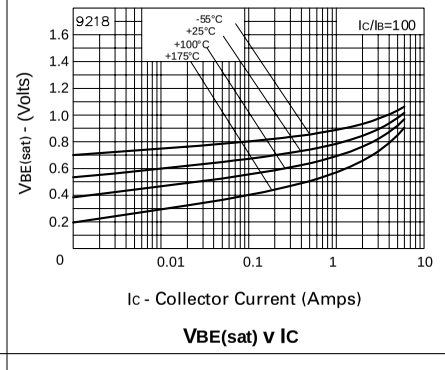
VCE(sat) v IC



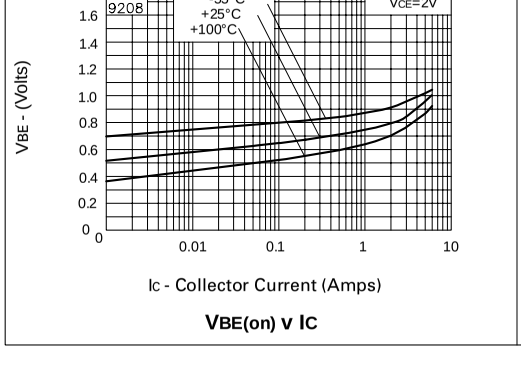
VCE(sat) v IC



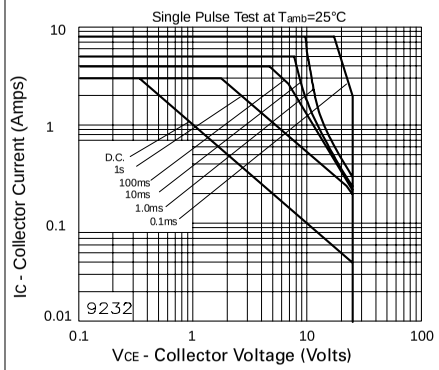
hFE v IC



VBE(sat) v IC



VBE(on) v IC



Safe Operating Area